

Mikael Å-stling

List of Publications by Year in descending order

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420
papers

9,127
citations

66315

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71651

76
g-index

430
all docs

430
docs citations

430
times ranked

8625
citing authors

#	ARTICLE	IF	CITATIONS
1	Improvement on Ge/GeOx/Tm ₂ O ₃ /HfO ₂ Gate Performance by Forming Gas Anneal. , 2021, , .		0
2	A Silicon Carbide 256 Pixel UV Image Sensor Array Operating at 400 Å°C. IEEE Journal of the Electron Devices Society, 2020, 8, 116-121.	1.2	8
3	Selective Epitaxial Growth of In Situ Doped SiGe on Bulk Ge for p+/n Junction Formation. Electronics (Switzerland), 2020, 9, 578.	1.8	0
4	Manufacture and characterization of graphene membranes with suspended silicon proof masses for MEMS and NEMS applications. Microsystems and Nanoengineering, 2020, 6, 17.	3.4	46
5	Process Conditions for Low Interface State Density in Si-passivated Ge Devices with TmSiO Interfacial Layer. ECS Journal of Solid State Science and Technology, 2020, 9, 125009.	0.9	1
6	Si-Passivated Ge Gate Stacks with Low Interface State and Oxide Trap Densities Using Thulium Silicate. ECS Transactions, 2020, 98, 387-393.	0.3	1
7	Editorial Exciting Progress. IEEE Journal of the Electron Devices Society, 2019, 7, 1-1.	1.2	2
8	Errata for "An Intermediate Frequency Amplifier for High-Temperature Applications" [Apr 18 1411-1418]. IEEE Transactions on Electron Devices, 2019, 66, 3694-3694.	1.6	0
9	Process Control and Optimization of 4H-SiC Semiconductor Devices and Circuits. , 2019, , .		1
10	Suspended Graphene Membranes with Attached Silicon Proof Masses as Piezoresistive Nanoelectromechanical Systems Accelerometers. Nano Letters, 2019, 19, 6788-6799.	4.5	36
11	Graphene ribbons with suspended masses as transducers in ultra-small nanoelectromechanical accelerometers. Nature Electronics, 2019, 2, 394-404.	13.1	70
12	Towards Silicon Carbide VLSI Circuits for Extreme Environment Applications. Electronics (Switzerland), 2019, 8, 496.	1.8	20
13	Utilizing the superior etch stop quality of HfO ₂ in the front end of line wafer scale integration of silicon nanowire biosensors. Microelectronic Engineering, 2019, 212, 13-20.	1.1	2
14	Fully inkjet printed ultrathin microsupercapacitors based on graphene electrodes and a nano-graphene oxide electrolyte. Nanoscale, 2019, 11, 10172-10177.	2.8	49
15	Wafer-scale HfO ₂ encapsulated silicon nanowire field effect transistor for efficient label-free DNA hybridization detection in dry environment. Nanotechnology, 2019, 30, 184002.	1.3	11
16	Pixel-based biosensor for enhanced control: silicon nanowires monolithically integrated with field-effect transistors in fully depleted silicon on insulator technology. Nanotechnology, 2019, 30, 225502.	1.3	5
17	Suppression of Short-Channel Effects in 4H-SiC Trench MOSFETs. Materials Science Forum, 2019, 963, 613-616.	0.3	3
18	Wet Transfer of Inkjet Printed Graphene for Microsupercapacitors on Arbitrary Substrates. ACS Applied Energy Materials, 2019, 2, 158-163.	2.5	24

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19	A 4H-SiC BJT as a Switch for On-Chip Integrated UV Photodiode. IEEE Electron Device Letters, 2019, 40, 51-54.	2.2	10
20	15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. IEEE Electron Device Letters, 2018, 39, 63-66.	2.2	37
21	Scaling and Modeling of High Temperature 4H-SiC p-i-n Photodiodes. IEEE Journal of the Electron Devices Society, 2018, 6, 139-145.	1.2	5
22	Germanium on Insulator Fabrication for Monolithic 3-D Integration. IEEE Journal of the Electron Devices Society, 2018, 6, 588-593.	1.2	7
23	Editorial Toward Faster Publishing and Shorter Turnaround Time. IEEE Journal of the Electron Devices Society, 2018, 6, 1-1.	1.2	3
24	Humidity and CO ₂ gas sensing properties of double-layer graphene. Carbon, 2018, 127, 576-587.	5.4	66
25	Investigation of Tm ₂ O ₃ As a Gate Dielectric for Ge MOS Devices. ECS Transactions, 2018, 86, 67-73.	0.3	3
26	Monolithic Wafer Scale Integration of Silicon Nanoribbon Sensors with CMOS for Lab-on-Chip Application. Micromachines, 2018, 9, 544.	1.4	3
27	Influence of Humidity on Contact Resistance in Graphene Devices. ACS Applied Materials & Interfaces, 2018, 10, 41738-41746.	4.0	17
28	4H-SiC pMOSFETs with Al-Doped S/D and NbNi Silicide Ohmic Contacts. Materials Science Forum, 2018, 924, 423-427.	0.3	1
29	An Intermediate Frequency Amplifier for High-Temperature Applications. IEEE Transactions on Electron Devices, 2018, 65, 1411-1418.	1.6	6
30	Inkjet-printing of graphene saturable absorbers for ~2 μm bulk and waveguide lasers. Optical Materials Express, 2018, 8, 2803.	1.6	7
31	A 600 °C TTL-based 11-stage Ring Oscillator in Bipolar Silicon Carbide Technology. IEEE Electron Device Letters, 2018, , 1-1.	2.2	20
32	Formation of nickel germanides from Ni layers with thickness below 10 nm. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, 020602.	0.6	4
33	Noninvasive Scanning Raman Spectroscopy and Tomography for Graphene Membrane Characterization. Nano Letters, 2017, 17, 1504-1511.	4.5	17
34	Bipolar integrated circuits in SiC for extreme environment operation. Semiconductor Science and Technology, 2017, 32, 034002.	1.0	28
35	An editorial on the recent advances in high and low temperature electronics. Semiconductor Science and Technology, 2017, 32, 080201.	1.0	2
36	Integration and High-Temperature Characterization of Ferroelectric Vanadium-Doped Bismuth Titanate Thin Films on Silicon Carbide. Journal of Electronic Materials, 2017, 46, 4478-4484.	1.0	4

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37	Graphene-based CO ₂ sensing and its cross-sensitivity with humidity. RSC Advances, 2017, 7, 22329-22339.	1.7	68
38	10+ kV Implantation-Free 4H-SiC PiN Diodes. Materials Science Forum, 2017, 897, 423-426.	0.3	1
39	Inkjet printed highly transparent and flexible graphene micro-supercapacitors. Nanoscale, 2017, 9, 6998-7005.	2.8	139
40	A Comprehensive Study on the Geometrical Effects in High-Power 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2017, 64, 882-887.	1.6	4
41	Wafer-Scale Statistical Analysis of Graphene FETs—Part I: Wafer-Scale Fabrication and Yield Analysis. IEEE Transactions on Electron Devices, 2017, 64, 3919-3926.	1.6	9
42	Wafer-Scale Statistical Analysis of Graphene Field-Effect Transistors—Part II: Analysis of Device Properties. IEEE Transactions on Electron Devices, 2017, 64, 3927-3933.	1.6	14
43	500 Å°C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. IEEE Electron Device Letters, 2017, 38, 1429-1432.	2.2	22
44	Scalable Fabrication and Integration of Graphene Microsupercapacitors through Full Inkjet Printing. ACS Nano, 2017, 11, 8249-8256.	7.3	280
45	The impact of atomic layer depositions on high quality Ge/GeO ₂ interfaces fabricated by rapid thermal annealing in O ₂ ambient. , 2017, , .		1
46	A Wafer-Scale Ni-Salicide Contact Technology on n-Type 4H-SiC. ECS Journal of Solid State Science and Technology, 2017, 6, P197-P200.	0.9	13
47	GOI fabrication for monolithic 3D integration. , 2017, , .		0
48	Scaling of 4H-SiC p-i-n photodiodes for high temperature applications. , 2017, , .		1
49	Gated base structure for improved current gain in SiC bipolar technology. , 2017, , .		1
50	Editorial Exciting Times for Our Journal. IEEE Journal of the Electron Devices Society, 2017, 5, 430-431.	1.2	0
51	Direct birefringence and transmission modulation via dynamic alignment of P3HT nanofibers in an advanced opto-fluidic component. Optical Materials Express, 2017, 7, 52.	1.6	4
52	Inkjet-Printing of Graphene Saturable Absorbers for ~2 Åµm Bulk and Waveguide Lasers. , 2017, , .		2
53	Electro-optical effects of high aspect ratio P3HT nanofibers colloid in polymer micro-fluid cells. Optics Letters, 2017, 42, 2157.	1.7	3
54	Optical birefringence from P3HT nanofibers in alternating electric field. , 2016, , .		0

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55	(Invited) TmSiO as a CMOS-Compatible High-k Dielectric. ECS Transactions, 2016, 72, 79-89.	0.3	0
56	Epitaxial Growth of Ge Strain Relaxed Buffer on Si with Low Threading Dislocation Density. ECS Transactions, 2016, 75, 615-621.	0.3	10
57	All-solid-state micro-supercapacitors based on inkjet printed graphene electrodes. Applied Physics Letters, 2016, 109, .	1.5	62
58	Modification of Etched Junction Termination Extension for the High Voltage 4H-SiC Power Devices. Materials Science Forum, 2016, 858, 978-981.	0.3	7
59	Graphene transfer methods for the fabrication of membrane-based NEMS devices. Microelectronic Engineering, 2016, 159, 108-113.	1.1	40
60	Bias-temperature instability on the back gate of single-layer double-gated graphene field-effect transistors. Japanese Journal of Applied Physics, 2016, 55, 04EP03.	0.8	6
61	(Invited) Emerging Graphene Device Technologies. ECS Transactions, 2016, 75, 17-35.	0.3	1
62	State of the art power switching devices in SiC and their applications. , 2016, , .		5
63	Intertwined Design: A Novel Lithographic Method to Realize Area Efficient High-Voltage SiC BJTs and Darlington Transistors. IEEE Transactions on Electron Devices, 2016, 63, 4366-4372.	1.6	6
64	Dynamic Manipulation of Optical Anisotropy of Suspended Poly(3-hexylthiophene) Nanofibers. Advanced Optical Materials, 2016, 4, 1651-1656.	3.6	5
65	Precise percolation thresholds of two-dimensional random systems comprising overlapping ellipses. Physica A: Statistical Mechanics and Its Applications, 2016, 462, 940-950.	1.2	21
66	Toward effective passivation of graphene to humidity sensing effects. , 2016, , .		3
67	Piezoresistive Properties of Suspended Graphene Membranes under Uniaxial and Biaxial Strain in Nanoelectromechanical Pressure Sensors. ACS Nano, 2016, 10, 9879-9886.	7.3	110
68	550 Å°C 4H-SiC p-i-n Photodiode Array With Two-Layer Metallization. IEEE Electron Device Letters, 2016, 37, 1594-1596.	2.2	24
69	Trilayer Graphene as a Candidate Material for Phase-Change Memory Applications. MRS Advances, 2016, 1, 1487-1494.	0.5	0
70	Size Impact of Ordered P3HT Nanofibers on Optical Anisotropy. Macromolecular Chemistry and Physics, 2016, 217, 1089-1095.	1.1	8
71	Sensitivity of the crystal quality of SiGe layers grown at low temperatures by trisilane and germane. Thin Solid Films, 2016, 613, 38-42.	0.8	1
72	Improved designs of Si-based quantum wells and Schottky diodes for IR detection. Thin Solid Films, 2016, 613, 19-23.	0.8	7

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73	Scalable Fabrication of 2D Semiconducting Crystals for Future Electronics. Electronics (Switzerland), 2015, 4, 1033-1061.	1.8	21
74	Electric field induced optical anisotropy of P3HT nanofibers in a liquid solution. Optical Materials Express, 2015, 5, 2642.	1.6	11
75	Hot-carrier degradation in single-layer double-gated graphene field-effect transistors. , 2015, , .		1
76	Influence of Passivation Oxide Thickness and Device Layout on the Current Gain of SiC BJTs. IEEE Electron Device Letters, 2015, 36, 11-13.	2.2	24
77	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. IEEE Electron Device Letters, 2015, 36, 168-170.	2.2	25
78	Step tunneling-enhanced hot-electron injection in vertical graphene base transistors. , 2015, , .		0
79	Integration of TmSiO/HfO ₂ Dielectric Stack in Sub-nm EOT High-k/Metal Gate CMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 934-939.	1.6	14
80	Conductivity scaling in supercritical percolation of nanoparticles “ not a power law. Nanoscale, 2015, 7, 3424-3428.	2.8	15
81	Large scale integration of graphene transistors for potential applications in the back end of the line. Solid-State Electronics, 2015, 108, 61-66.	0.8	19
82	Optimizing the optical and electrical properties of graphene ink thin films by laser-annealing. 2D Materials, 2015, 2, 011003.	2.0	26
83	Bilayer insulator tunnel barriers for graphene-based vertical hot-electron transistors. Nanoscale, 2015, 7, 13096-13104.	2.8	48
84	Conductivity modulated on-axis 4H-SiC 10+kV PiN diodes. , 2015, , .		18
85	Threshold voltage control in TmSiO/HfO ₂ high-k/metal gate MOSFETs. Solid-State Electronics, 2015, 108, 24-29.	0.8	4
86	Impact of hot carrier stress on the defect density and mobility in double-gated graphene field-effect transistors. , 2015, , .		1
87	Residual Metallic Contamination of Transferred Chemical Vapor Deposited Graphene. ACS Nano, 2015, 9, 4776-4785.	7.3	250
88	Low-Frequency Noise Characterization of Ultra-Low Equivalent-Oxide-Thickness Thulium Silicate Interfacial Layer nMOSFETs. IEEE Electron Device Letters, 2015, 36, 1355-1358.	2.2	1
89	Resistive graphene humidity sensors with rapid and direct electrical readout. Nanoscale, 2015, 7, 19099-19109.	2.8	252
90	Hot-Carrier Degradation and Bias-Temperature Instability in Single-Layer Graphene Field-Effect Transistors: Similarities and Differences. IEEE Transactions on Electron Devices, 2015, 62, 3876-3881.	1.6	23

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91	Atomic-layer deposited thulium oxide as a passivation layer on germanium. Journal of Applied Physics, 2015, 117, .	1.1	4
92	Optimal Emitter Cell Geometry in High Power 4H-SiC BJTs. IEEE Electron Device Letters, 2015, 36, 1069-1072.	2.2	9
93	Enhanced Channel Mobility at Sub-nm EOT by Integration of a TmSiO Interfacial Layer in HfO ₂ /TiN High-k/Metal Gate MOSFETs. IEEE Journal of the Electron Devices Society, 2015, 3, 397-404.	1.2	5
94	Going ballistic: Graphene hot electron transistors. Solid State Communications, 2015, 224, 64-75.	0.9	37
95	Area- and efficiency-optimized junction termination for a 5.6 kV SiC BJT process with low ON-resistance. , 2015, , .		13
96	Characterization of bonding surface and electrical insulation properties of inter layer dielectrics for 3D monolithic integration. , 2015, , .		3
97	Interplay between hot carrier and bias stress components in single-layer double-gated graphene field-effect transistors. , 2015, , .		1
98	Electro-optical response of P3HT nanofibers in liquid solution. , 2015, , .		0
99	Chemical vapor deposited graphene: From synthesis to applications. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2439-2449.	0.8	81
100	SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs. Materials Science Forum, 2014, 778-780, 1005-1008.	0.3	18
101	Bias-temperature instability in single-layer graphene field-effect transistors: A reliability challenge. , 2014, , .		3
102	Graphene-based piezoresistive pressure sensing for uniaxial and biaxial strains. , 2014, , .		2
103	Recent advances in high-k dielectrics and inter layer engineering. , 2014, , .		3
104	Characterization of La _x Hf _y O Gate Dielectrics in 4H-SiC MOS Capacitor. Materials Science Forum, 2014, 778-780, 549-552.	0.3	2
105	Interfacial Layer Engineering Using Thulium Silicate/Germanate for High-k/Metal Gate MOSFETs. ECS Transactions, 2014, 64, 249-260.	0.3	2
106	(Invited) Interface Engineering Routes for a Future CMOS Ge-Based Technology. ECS Transactions, 2014, 61, 73-88.	0.3	2
107	CVD Growth of GeSnSiC Alloys Using Disilane, Digermane, Tin Tetrachloride and Methylsilane. ECS Transactions, 2014, 64, 703-710.	0.3	7
108	Silicon nanowires integrated with CMOS circuits for biosensing application. Solid-State Electronics, 2014, 98, 26-31.	0.8	15

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109	New materials for post-Si computing. MRS Bulletin, 2014, 39, 658-662.	1.7	15
110	Bias-temperature instability in single-layer graphene field-effect transistors. Applied Physics Letters, 2014, 105, .	1.5	37
111	Effective workfunction control in TmSiO/HfO ₂ high-k/metal gate stacks. , 2014, , .		2
112	Fabrication and characterization of silicon nanowires using STL for biosensing applications. , 2014, , .		3
113	Integrating 3D PIN germanium detectors with high-k ALD fabricated slot waveguides. , 2014, , .		3
114	Static Nonlinearity in Graphene Field Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 3001-3003.	1.6	14
115	PDMS-supported graphene transfer using intermediary polymer layers. , 2014, , .		3
116	Fabrication of strained Ge on insulator via room temperature wafer bonding. , 2014, , .		1
117	Embedded graphene photodetectors for silicon photonics. , 2014, , .		2
118	Inkjet Printing of MoS ₂ . Advanced Functional Materials, 2014, 24, 6524-6531.	7.8	210
119	Effects of carbon pre-silicidation implant into Si substrate on NiSi. Microelectronic Engineering, 2014, 120, 178-181.	1.1	14
120	Dependence of the colored frequency noise in spin torque oscillators on current and magnetic field. Applied Physics Letters, 2014, 104, 092405.	1.5	28
121	Biaxial strain in suspended graphene membranes for piezoresistive sensing. , 2014, , .		5
122	Inkjet Printing of 2D Layered Materials. ChemPhysChem, 2014, 15, 3427-3434.	1.0	78
123	Variation of Schottky barrier height induced by dopant segregation monitored by contact resistivity measurements. Microelectronic Engineering, 2014, 120, 174-177.	1.1	7
124	Wafer scale graphene transfer for back end of the line device integration. , 2014, , .		4
125	A Comprehensive Graphene FET Model for Circuit Design. IEEE Transactions on Electron Devices, 2014, 61, 1199-1206.	1.6	122
126	Electrical characterization of thulium silicate interfacial layers for integration in high-k/metal gate CMOS technology. Solid-State Electronics, 2014, 98, 20-25.	0.8	5

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127	Lateral p-n-p Transistors and Complementary SiC Bipolar Technology. IEEE Electron Device Letters, 2014, 35, 428-430.	2.2	17
128	Fabrication of Relaxed Germanium on Insulator via Room Temperature Wafer Bonding. ECS Transactions, 2014, 64, 533-541.	0.3	2
129	Improved low-frequency noise for 0.3nm EOT thulium silicate interfacial layer. , 2014, , .		1
130	Thulium Silicate Interfacial Layer for Scalable High-k/Metal Gate Stacks. IEEE Transactions on Electron Devices, 2013, 60, 3271-3276.	1.6	19
131	Growth of GeSnSiC layers for photonic applications. Surface and Coatings Technology, 2013, 230, 106-110.	2.2	9
132	A study of low-frequency noise on high-k/metal gate stacks with in situ SiO ₂ interfacial layer. , 2013, , .		2
133	Silicon nanowires integrated in a fully depleted CMOS process for charge based biosensing. , 2013, , .		2
134	Mobility enhancement by integration of TmSiO IL in 0.65nm EOT high-k/metal gate MOSFETs. , 2013, , .		4
135	500 ^{nm} Bipolar Integrated OR/NOR Gate in 4H-SiC. IEEE Electron Device Letters, 2013, 34, 1091-1093.	2.2	80
136	Interface engineering of Ge using thulium oxide: Band line-up study. Microelectronic Engineering, 2013, 109, 204-207.	1.1	9
137	Pressure sensors based on suspended graphene membranes. Solid-State Electronics, 2013, 88, 89-94.	0.8	70
138	A Graphene-Based Hot Electron Transistor. Nano Letters, 2013, 13, 1435-1439.	4.5	215
139	A manufacturable process integration approach for graphene devices. Solid-State Electronics, 2013, 84, 185-190.	0.8	24
140	Efficient Inkjet Printing of Graphene. Advanced Materials, 2013, 25, 3985-3992.	11.1	425
141	Electromechanical Piezoresistive Sensing in Suspended Graphene Membranes. Nano Letters, 2013, 13, 3237-3242.	4.5	332
142	Simulation of low Schottky barrier MOSFETs using an improved Multi-subband Monte Carlo model. Solid-State Electronics, 2013, 79, 172-178.	0.8	2
143	Low loss high-k slot waveguides for silicon photonics. , 2013, , .		2
144	Strain Engineering in GeSnSi Materials. ECS Transactions, 2013, 50, 527-531.	0.3	22

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145	Process Variation Tolerant 4H-SiC Power Devices Utilizing Trench Structures. Materials Science Forum, 2013, 740-742, 809-812.	0.3	1
146	High-Temperature Characterization of 4H-SiC Darlington Transistors for Low Voltage Applications. Materials Science Forum, 2013, 740-742, 966-969.	0.3	2
147	A 4H-SiC Bipolar Technology for High-Temperature Integrated Circuits. Journal of Microelectronics and Electronic Packaging, 2013, 10, 155-162.	0.8	10
148	Characterization of SiGe/Si multi-quantum wells for infrared sensing. Applied Physics Letters, 2013, 103, .	1.5	5
149	Graphene base hot electron transistors with high on/off current ratios. , 2013, , .		0
150	High-Deposition-Rate Atomic Layer Deposition of Thulium Oxide from $TmCp_3$ and H_2O . Journal of the Electrochemical Society, 2013, 160, D538-D542.	1.3	14
151	Percolation thresholds of two-dimensional continuum systems of rectangles. Physical Review E, 2013, 88, 012101.	0.8	43
152	SiC device technology for energy efficiency and high temperature operation. , 2013, , .		0
153	Characterization of thulium silicate interfacial layer for high-k/metal gate MOSFETs. , 2013, , .		1
154	Prevention of Graphene Restacking for Performance Boost of Supercapacitors—A Review. Crystals, 2013, 3, 163-190.	1.0	98
155	Double slot high-k waveguide grating couplers for silicon photonics. , 2012, , .		2
156	Threshold of hierarchical percolating systems. Physical Review E, 2012, 85, 021109.	0.8	17
157	Atomic layer deposition-based interface engineering for high-k/metal gate stacks. , 2012, , .		1
158	RF Performance Projections of Graphene FETs vs. Silicon MOSFETs. ECS Solid State Letters, 2012, 1, Q39-Q41.	1.4	24
159	Low-frequency noise in high-k LaLuO ₃ /TiN MOSFETs. Solid-State Electronics, 2012, 78, 51-55.	0.8	11
160	Strain engineering in suspended graphene devices for pressure sensor applications. , 2012, , .		13
161	An integration approach for graphene double-gate transistors. , 2012, , .		5
162	CMOS compatible ALD high-k double slot grating couplers for on-chip optical interconnects. , 2012, , .		1

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163	In situ SiO ₂ interfacial layer formation for scaled ALD high-k/metal gate stacks. , 2012, , .		8
164	Corrected finite-size scaling in percolation. Physical Review E, 2012, 86, 040105.	0.8	9
165	Impact of oxidation and reduction annealing on the electrical properties of Ge/La ₂ O ₃ /ZrO ₂ gate stacks. Solid-State Electronics, 2012, 74, 7-12.	0.8	8
166	ALD high-k layer grating couplers for single and double slot on-chip SOI photonics. Solid-State Electronics, 2012, 74, 58-63.	0.8	6
167	Alternative graphene devices: beyond field effect transistors. , 2012, , .		2
168	Graphene for More Moore and More Than Moore applications. , 2012, , .		4
169	High performance infra-red detectors based on Si/SiGe multilayers quantum structure. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 1563-1566.	1.7	7
170	Kinetic Modeling of Low Temperature Epitaxy Growth of SiGe Using Disilane and Digermane. Journal of the Electrochemical Society, 2012, 159, H478-H481.	1.3	6
171	Vertical Graphene Base Transistor. IEEE Electron Device Letters, 2012, 33, 691-693.	2.2	141
172	A simple route towards high-concentration surfactant-free graphene dispersions. Carbon, 2012, 50, 3113-3116.	5.4	45
173	Design and Characterization of High-Temperature ECL-Based Bipolar Integrated Circuits in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 1076-1083.	1.6	56
174	Error Propagation in Contact Resistivity Extraction Using Cross-Bridge Kelvin Resistors. IEEE Transactions on Electron Devices, 2012, 59, 1585-1591.	1.6	7
175	Fully etched grating couplers for atomic layer deposited horizontal slot waveguides. , 2011, , .		3
176	Removal of Crystal Orientation Effects on the Current Gain of 4H-SiC BJTs Using Surface Passivation. IEEE Electron Device Letters, 2011, 32, 596-598.	2.2	6
177	ALD high-k layer grating couplers for single and double slot on-chip SOI photonics. , 2011, , .		1
178	High Current-Gain Implantation-Free 4H-SiC Monolithic Darlington Transistor. IEEE Electron Device Letters, 2011, 32, 188-190.	2.2	4
179	On the role of Coulomb scattering in hafnium-silicate gated silicon n and p-channel metal-oxide-semiconductor-field-effect-transistors. Journal of Applied Physics, 2011, 110, 124503.	1.1	2
180	Ink-jet printed thin-film transistors with carbon nanotube channels shaped in long strips. Journal of Applied Physics, 2011, 109, 084915.	1.1	20

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181	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2011, 58, 259-265.	1.6	57
182	Modeling and Characterization of the on-Resistance in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2011, 58, 2081-2087.	1.6	20
183	On Different Process Schemes for MOSFETs With a Controllable NiSi-Based Metallic Source/Drain. IEEE Transactions on Electron Devices, 2011, 58, 1898-1906.	1.6	19
184	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. IEEE Transactions on Electron Devices, 2011, 58, 2665-2669.	1.6	26
185	SiC power devices — Present status, applications and future perspective. , 2011, , .		223
186	High power devices in wide bandgap semiconductors. Science China Information Sciences, 2011, 54, 1087-1093.	2.7	18
187	The performance improvement evaluation for SiGe-based IR detectors. Solid-State Electronics, 2011, 62, 72-76.	0.8	21
188	SiC bipolar devices for high power and integrated drivers. , 2011, , .		5
189	A Hysteresis-Free High-k Dielectric and Contact Resistance Considerations for Graphene Field Effect Transistors. ECS Transactions, 2011, 41, 165-171.	0.3	19
190	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 704-711.	1.6	56
191	Strained-Silicon Heterojunction Bipolar Transistor. IEEE Transactions on Electron Devices, 2010, 57, 1243-1252.	1.6	12
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